

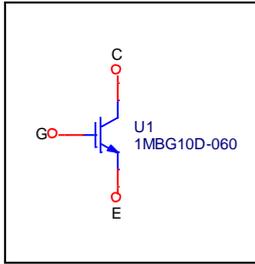
Device Modeling Report

COMPONENTS: Insulated Gate Bipolar Transistor (IGBT)
PART NUMBER: 1MBG10D-060
MANUFACTURER: FUJI ELECTRIC



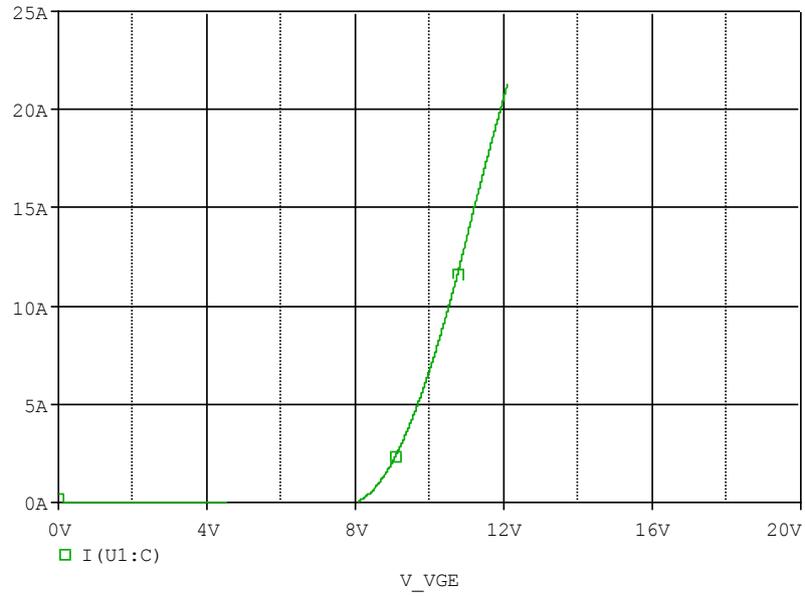
Bee Technologies Inc.

Circuit Configuration

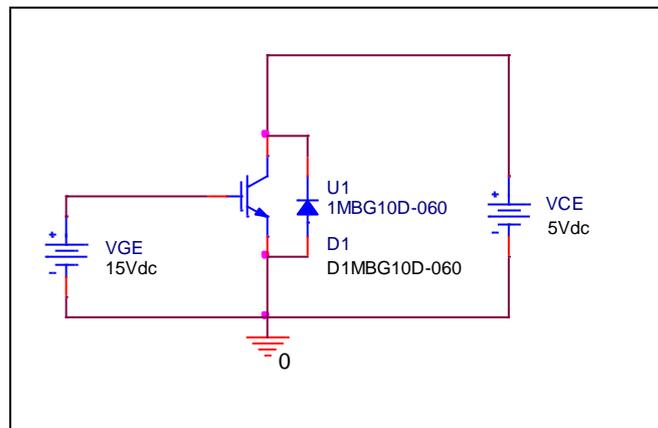


Transfer Characteristics

Circuit Simulation result

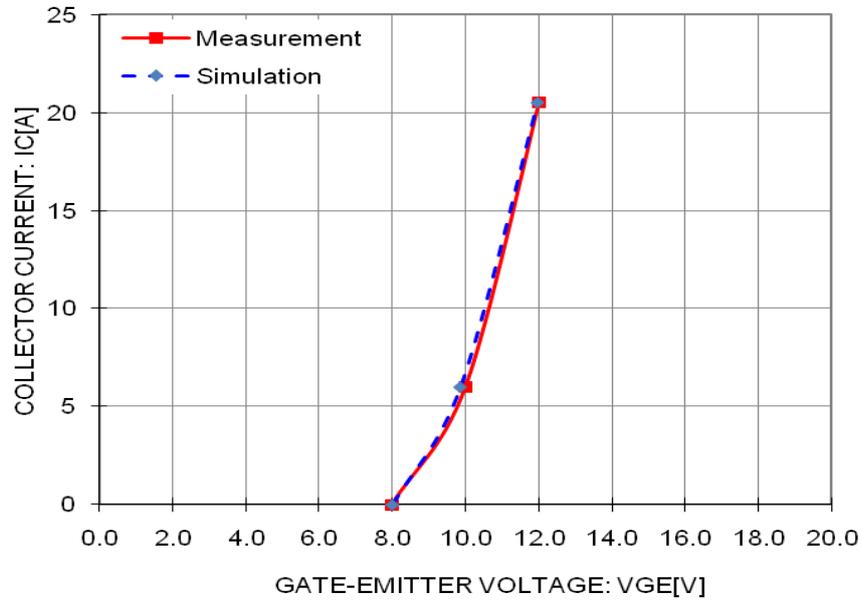


Evaluation circuit



Comparison Graph

Simulation result



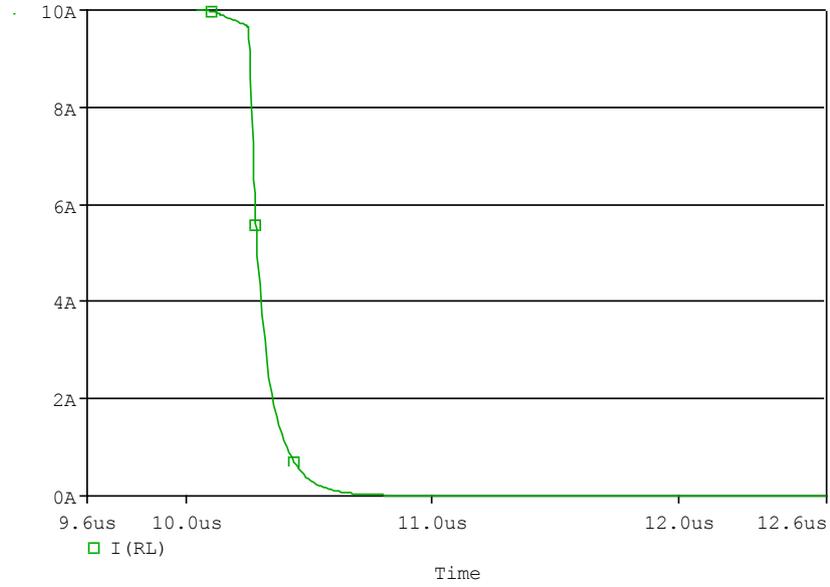
Comparison table

Test condition: $V_{CE} = 5$ (V)

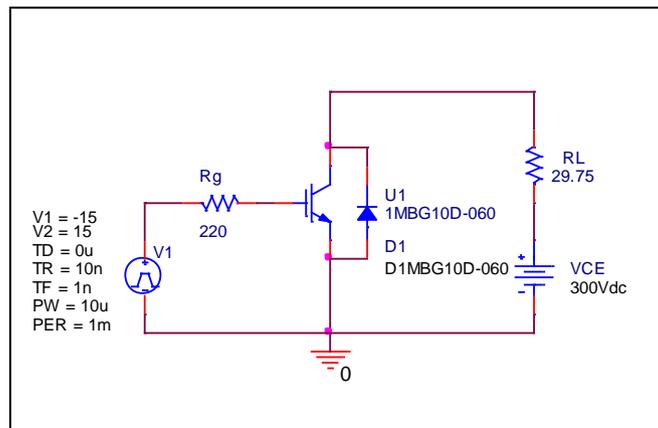
| IC (A) | VGE (V) | | %Error |
|--------|-------------|------------|--------|
| | Measurement | Simulation | |
| 0.000 | 8.000 | 8.017 | 0.21 |
| 6.000 | 10.000 | 9.870 | -1.30 |
| 20.500 | 12.000 | 11.983 | -0.14 |

Fall Time Characteristics

Circuit Simulation result



Evaluation circuit

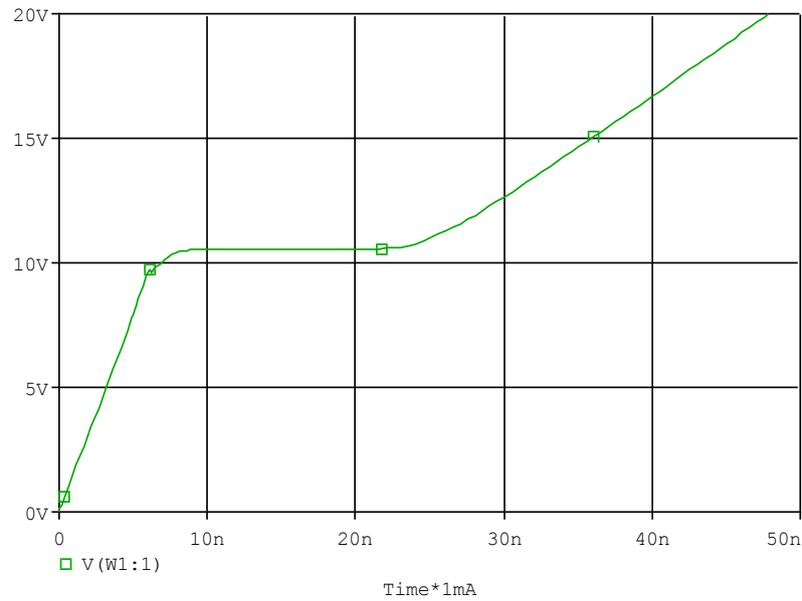


Test condition: $I_C=10$ (A), $V_{CC}=300$ (V)

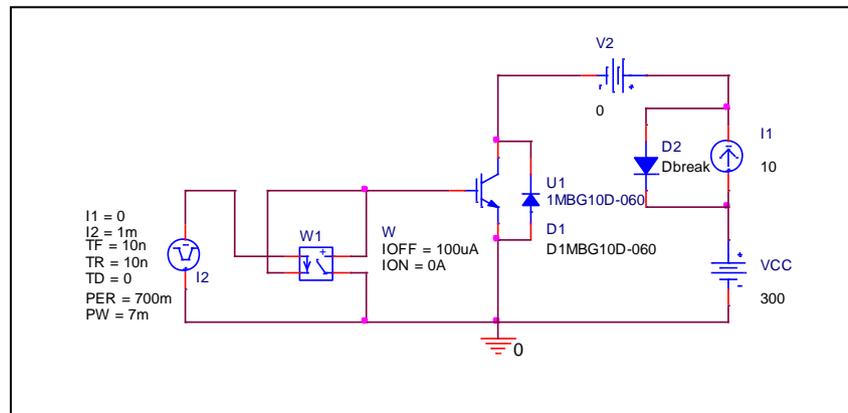
| Parameter | Unit | Measurement | Simulation | %Error |
|-----------|------|-------------|------------|--------|
| tf | us | 0.150 | 0.148 | -1.41 |

Gate Charge Characteristics

Circuit Simulation result



Evaluation circuit

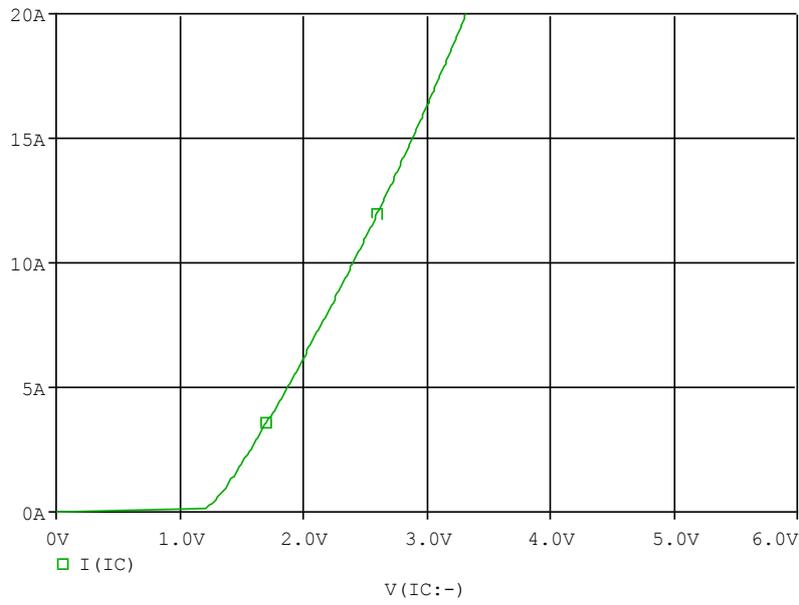


Test condition: $V_{CC}=300$ (V), $I_C=10$ (A), $V_{GE}=15$ (V)

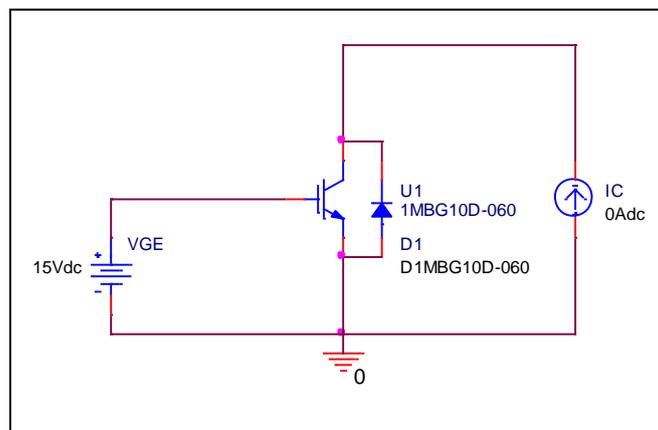
| Parameter | Unit | Measurement | Simulation | %Error |
|------------|-----------|---------------|---------------|--------------|
| Qge | nc | 6.000 | 6.035 | 0.58 |
| Qgc | nc | 17.500 | 16.848 | -3.73 |
| Qg | nc | 35.600 | 35.952 | 0.99 |

Saturation Characteristics

Circuit Simulation result

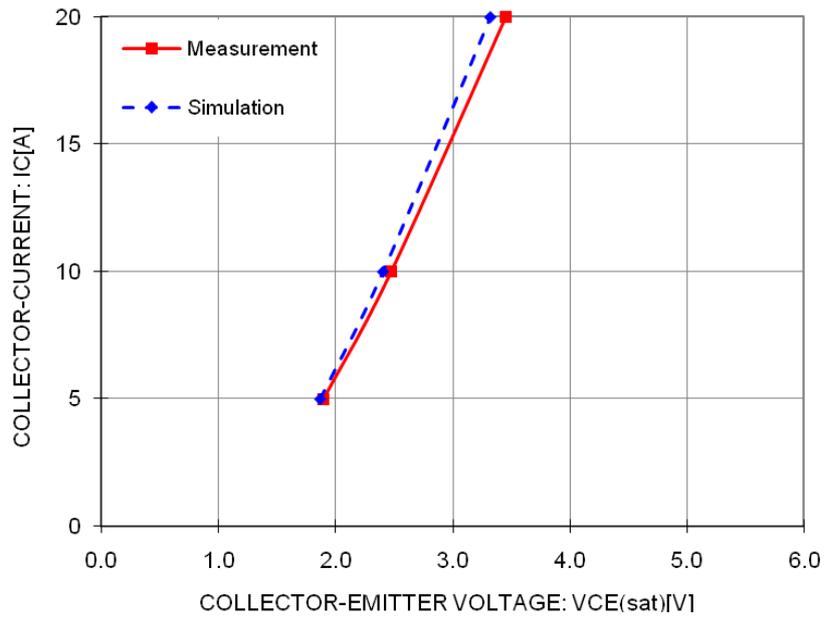


Evaluation circuit



Comparison Graph

Simulation result



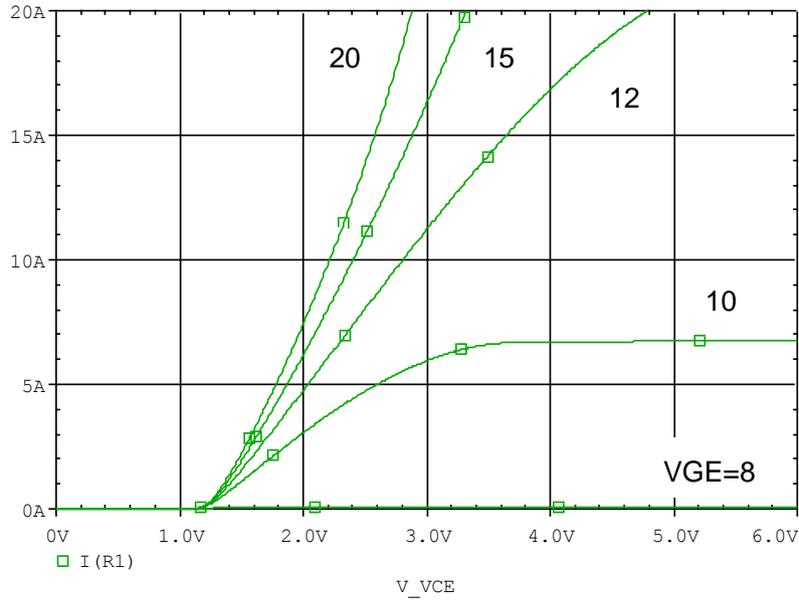
Comparison table

Test condition: $V_{GE} = 15$ (V)

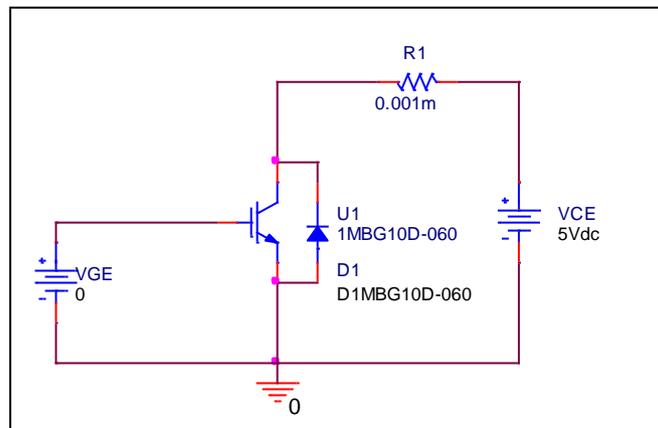
| Ic(A) | VCE (V) | | %Error |
|-------|-------------|------------|--------|
| | Measurement | Simulation | |
| 5 | 1.900 | 1.869 | -1.63 |
| 10 | 2.475 | 2.404 | -2.87 |
| 20 | 3.450 | 3.319 | -3.79 |

Output Characteristics

Circuit Simulation result

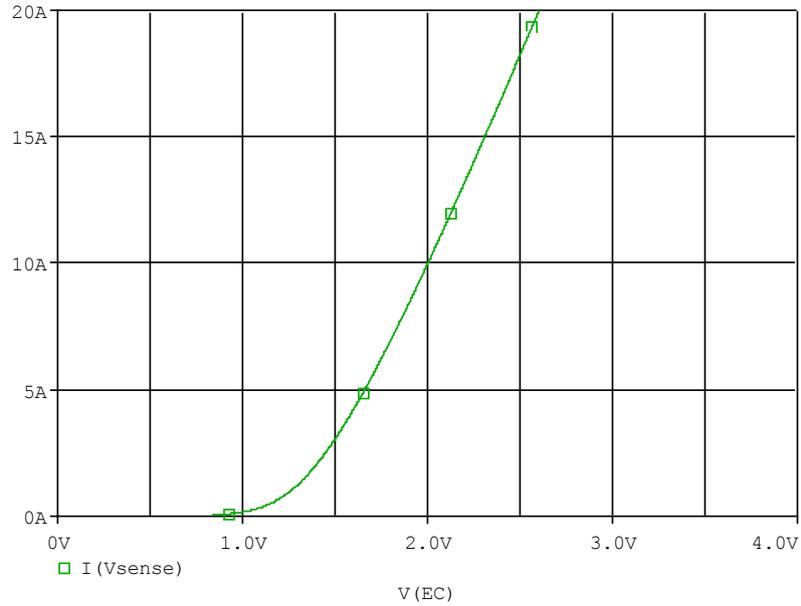


Evaluation circuit

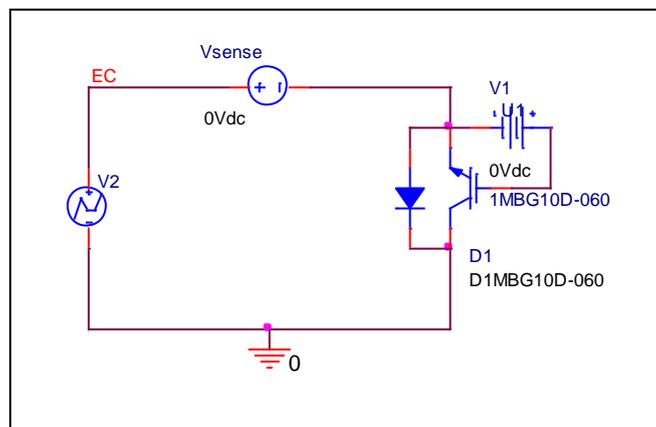


FWD Forward Current Characteristics

Circuit Simulation result

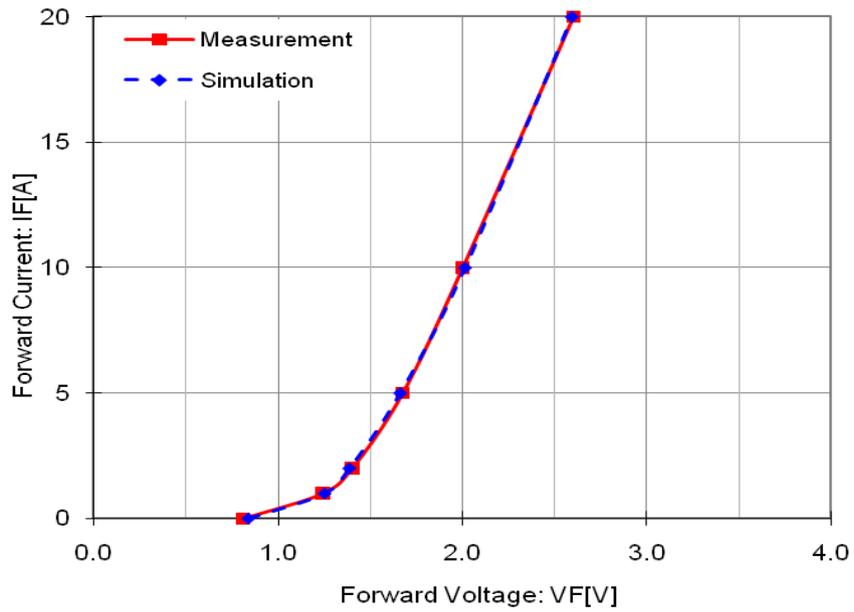


Evaluation circuit



Comparison Graph

Simulation result

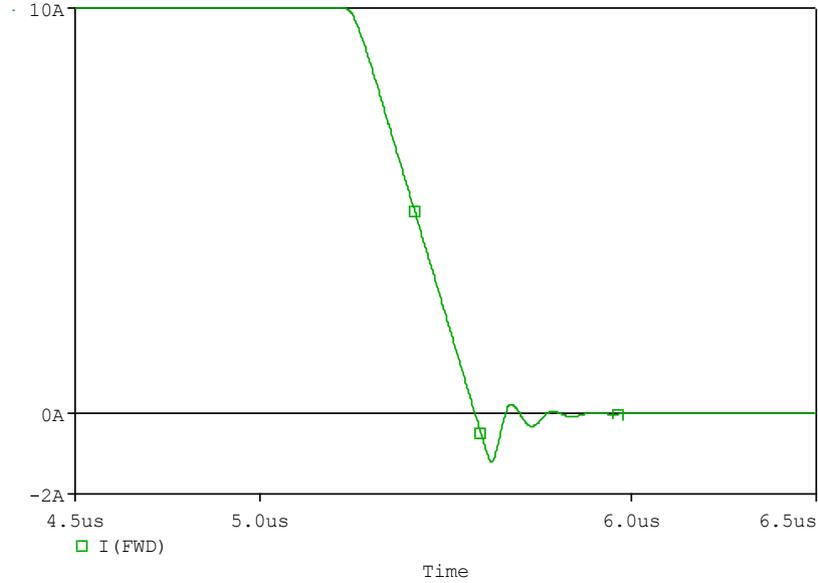


Comparison table

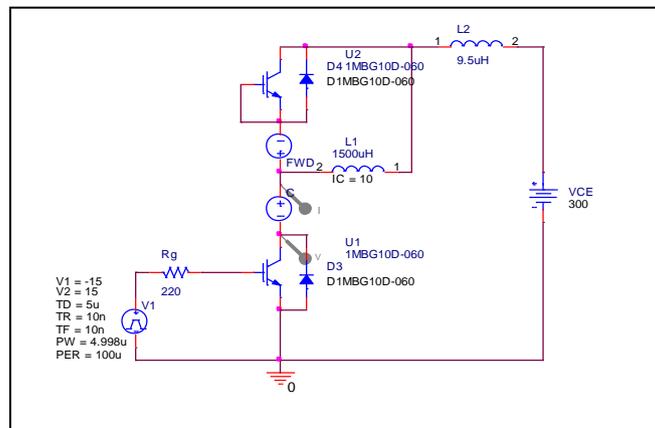
| IF(A) | VF (V) | | %Error |
|-------|-------------|------------|--------|
| | Measurement | Simulation | |
| 0 | 0.810 | 0.840 | 3.70 |
| 1 | 1.240 | 1.253 | 1.01 |
| 2 | 1.400 | 1.388 | -0.86 |
| 5 | 1.675 | 1.664 | -0.64 |
| 10 | 2.000 | 2.015 | 0.72 |
| 20 | 2.600 | 2.596 | -0.15 |

Reverse Recovery Characteristics

Circuit Simulation result



Evaluation circuit



Test condition: $V_{CC}=300 (V)$, $I_C=10 (A)$

| Parameter | Unit | Measurement | Simulation | %Error |
|-----------|------|-------------|------------|--------|
| trr | nsec | 125.000 | 79.876 | -36.10 |
| Irr | A | 1.200 | 1.198 | -0.17 |